3DD159(161), 3DD162(163)

NPN Silicon Low Frequency High Power Transistor

Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications					
			3DD159			3DD162		
			A	B	C	D	E	F
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300
			3DD159: I_C=3mA			3DD162: I_C=3mA		
C-Base Breakdown Voltage	$V_{(BR)CBO}$	V	80	150	200	250	350	400
			3DD159: I_C=3mA			3DD162: I_C=3mA		
Emitter-Base Voltage	V_{EBO}	V	5			5		
Max. Collector Current	I_{CM}	A	5.0			7.5		
Max. Collector Dissipation	P_{CM}	W	50 (T_c≤75°C)			75 (T_c≤75°C)		
Junction Temperature	T_{jm}	°C	175					
Storage Temperature	T_{stg}	°C	-55~+175					
Collector-Emitter Leakage Current	I_{CEO}	mA	1.0 (A:V_{CE}=30V;B:V_{CE}=50V; C~F:V_{CE}=100V)					
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.2 (I_C=2.5A,I_B=0.25A)			1.2 (I_C=3.75A, I_B=0.38A)		
DC Current Gain	h_{FE}		Max.:180,Min.:15 (V_{CE}=5V,I_C=2.5A)			Max.:180, Min.:15 (V_{CE}=5V,I_C=3.75A)		
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥5 (I_E=1mA)			≥5 (I_E=2mA)		

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions:

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